



September, 2013

SJ-FET

TSA20N60S, TSK20N60S 600V N-Channel MOSFET

Description

SJ-FET is new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance.

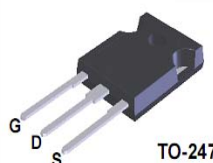
This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. SJ-FET is suitable for various AC/DC power conversion inswitching mode operation for higher efficiency.

Features

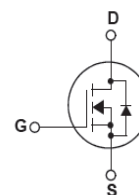
- 650V @TJ = 150 °C
- Typ. RDS(on) = 0.16 Ω
- Ultra Low Gate Charge (typ. Qg = 63nC)
- 100% avalanche tested
- Rohs Compliant



TO-3P



TO-247



Absolute Maximum Ratings

Symbol	Parameter	TSA_K20N60S	Unit
V _{DSS}	Drain-Source Voltage	600	V
I _D	Drain Current -Continuous (TC = 25°C) -Continuous (TC = 100°C)	20* 10*	A
I _{DM}	Drain Current - Pulsed (Note 1)	62*	A
V _{GSS}	Gate-Source voltage	±30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	525	mJ
I _{AR}	Avalanche Current (Note 1)	20	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	1	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P _D	Power Dissipation (TC = 25°C) -Derate above 25°C	151 1.67	W W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	°C

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	TSA_K20N60S	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case	0.83	°C/W
R _{θCS}	Thermal Resistance, Case-to-Sink Typ.	0.5	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	62	°C/W

TSA20N60S, TSK20N60S 600V N-Channel MOSFET

Electrical Characteristics TC = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Off Characteristics						
BVDSS	Drain-Source Breakdown Voltage	VGS = 0V, ID = 250μA, TJ = 25℃	600	--	--	V
		VGS = 0V, ID = 250μA, TJ = 150℃	--	650	--	V
Δ BVDSS / Δ TJ	Breakdown Voltage Temperature Coefficient	ID = 250μA, Referenced to 25℃	--	0.6	--	V/℃
IDSS	Zero Gate Voltage Drain Current	VDS = 600V, VGS = 0V VDS =480V, TC = 125℃	--	--	1 10	μA μA
IGTSF	Gate-Body Leakage Current, Forward	VGS = 30V, VDS = 0V	--	--	100	nA
IGSSR	Gate-Body Leakage Current, Reverse	VGS = -30V, VDS = 0V	--	--	-100	nA
On Characteristics						
VGS(th)	Gate Threshold Voltage	VDS = VGS, ID = 250μA	2.5	--	4.5	V
RDS(on)	Static Drain-Source On-Resistance	VGS = 10V, ID = 10A	--	0.16	0.19	Ω
gFS	Forward Transconductance	VDS = 40V, ID =5A (Note 4)	--	16	--	S
Rg	Gate Resistance	F=1MHz, open drain	--	4.5	--	Ω
Dynamic Characteristics						
Ciss	Input Capacitance	VDS = 25V, VGS = 0V, f = 1.0MHz	--	1440	--	pF
Coss	Output Capacitance		--	300	--	pF
Crss	Reverse Transfer Capacitance		--	10	--	pF
Switching Characteristics						
td(on)	Turn-On Delay Time	VDD = 400V, ID = 10A RG = 20 Ω (Note 4, 5)	--	25	--	ns
tr	Turn-On Rise Time		--	55	--	ns
td(off)	Turn-Off Delay Time		--	70	--	ns
tf	Turn-Off Fall Time		--	40	--	ns
Qg	Total Gate Charge	VDS = 480V, ID = 20A VGS = 10V (Note 4, 5)	--	63	--	nC
Qgs	Gate-Source Charge		--	7.8	--	nC
Qgd	Gate-Drain Charge		--	9	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
IS	Maximum Continuous Drain-Source Diode Forward Current		--	--	20	A
ISM	Maximum Pulsed Drain-Source Diode Forward Current		--	--	60	A
VSD	Drain-Source Diode Forward Voltage	VGS = 0V, IS = 20A	--	--	1.5	V
trr	Reverse Recovery Time	VGS = 0V, IS = 20A dIF/dt =100A/μs (Note 4)	--	475	--	ns
Qrr	Reverse Recovery Charge		--	5.8	--	μC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L=10.5mH, I_{AS}=10A, VDD=150V, Starting TJ=25 °C
3. I_{SD}≤20A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting TJ = 25 °C
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

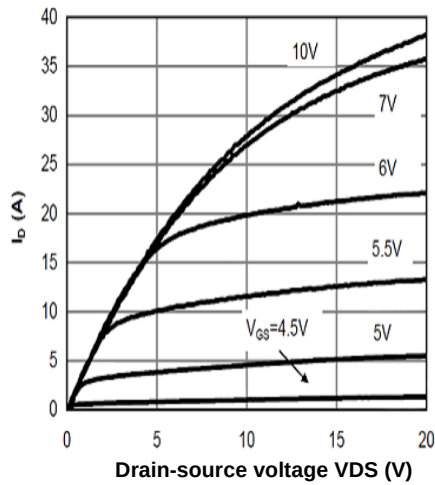


Figure 1: On-Region Characteristics@25° C

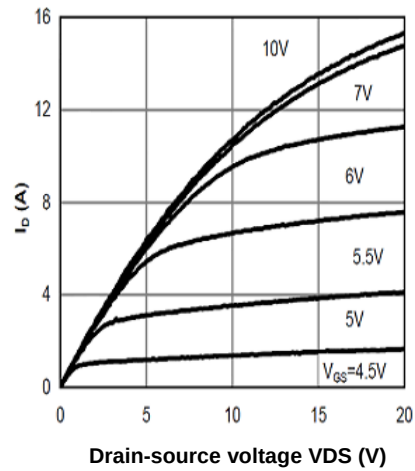


Figure 2: On-Region Characteristics@125° C

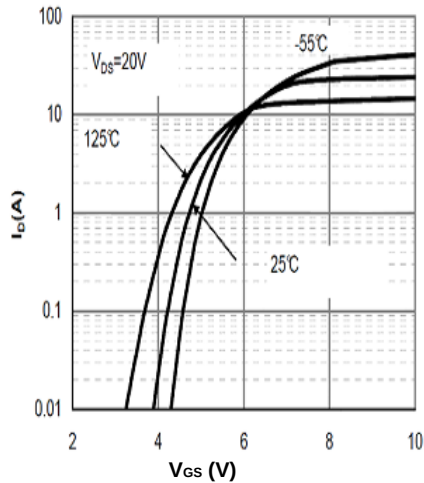


Figure 3: Transfer Charateristics

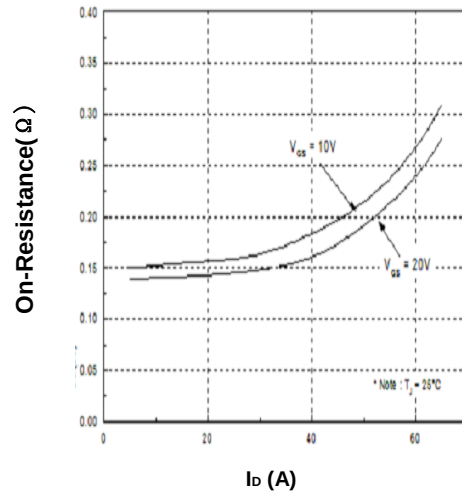


Figure 4: On-Resistance vs. Drain Current (I_D)

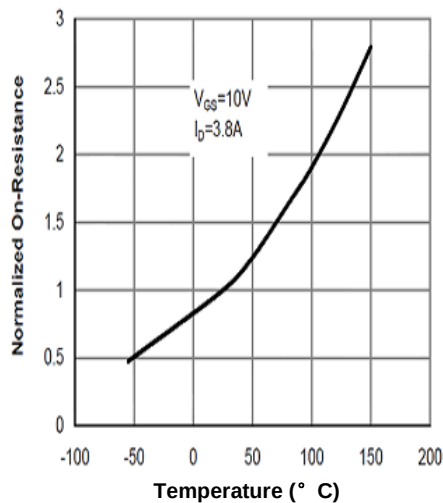


Figure 5: On-Resistance vs. Junction Temperature

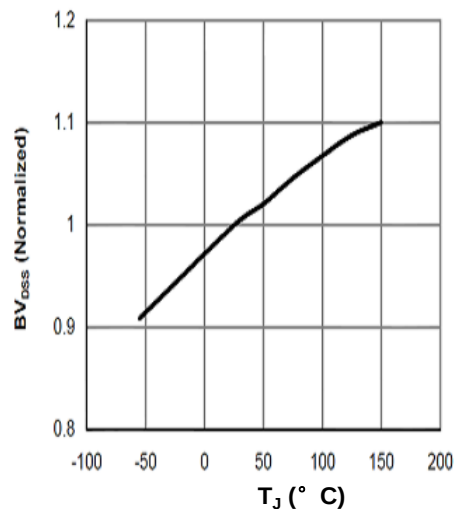


Figure 6: Break Down vs. Junction Temperature

Typical Performance Characteristics

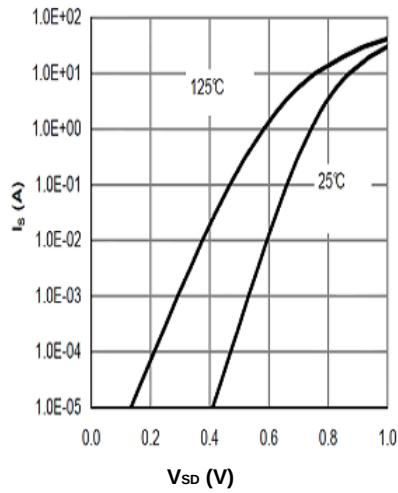


Figure 7: Body-Diode Characteristics

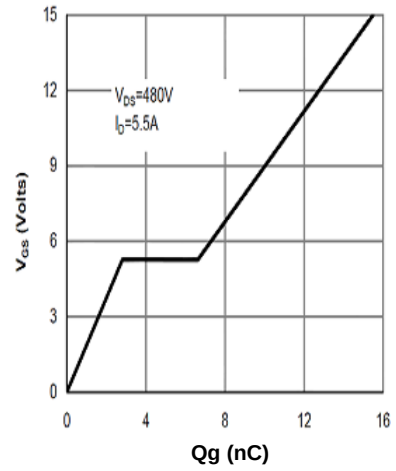


Figure 8: Gate-Charge Characteristics

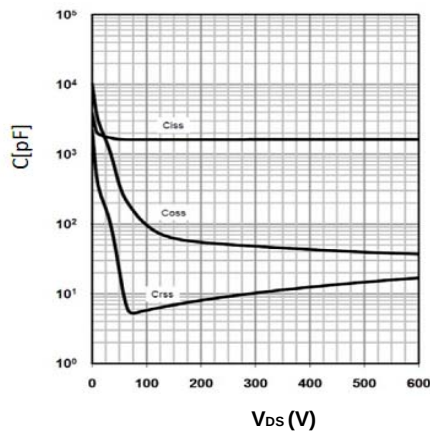


Figure 9: Capacitance Characteristics
 $C=f(V_{DS}), V_{GS}=0V, f=1MHz$

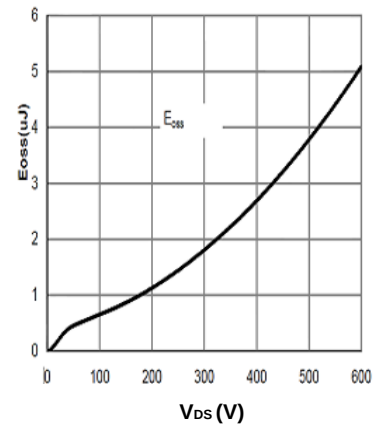


Figure 10: C_{oss} stored Energy

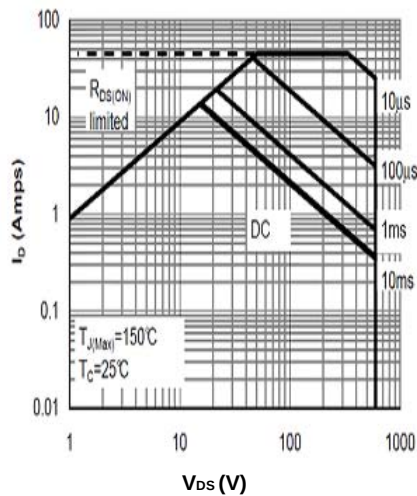


Figure 11: Maximum Forward Biased
Safe Operating Area

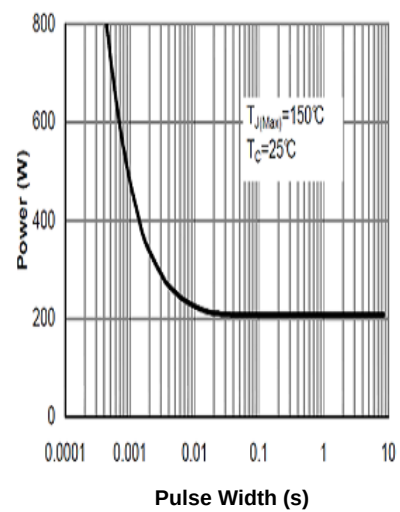


Figure 12: Single Pulse Power Rating
Junction to Case

Typical Performance Characteristics

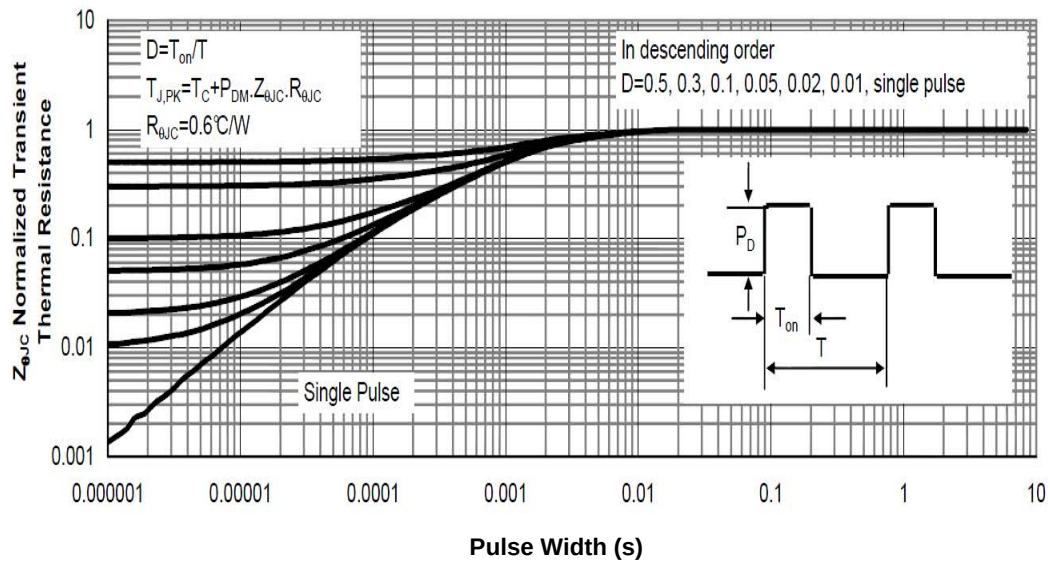


Figure 12: Normalized Maximum Transient Thermal Impedance

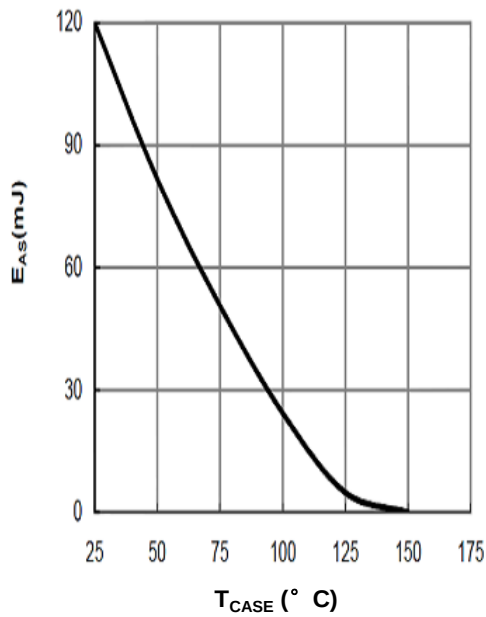


Figure 13: Avalanche energy

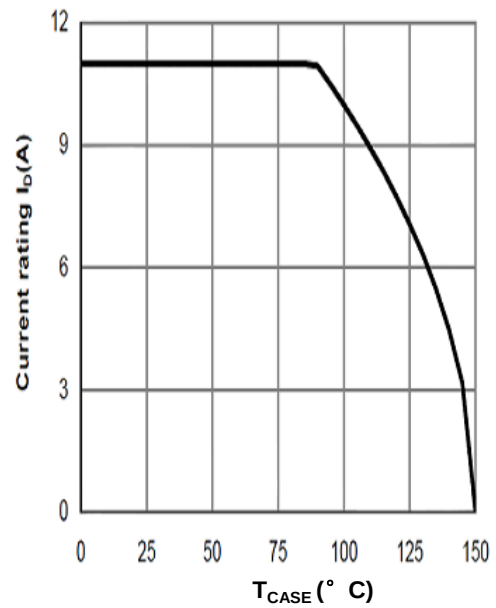


Figure 14: Current De-rating

Typical Performance Characteristics

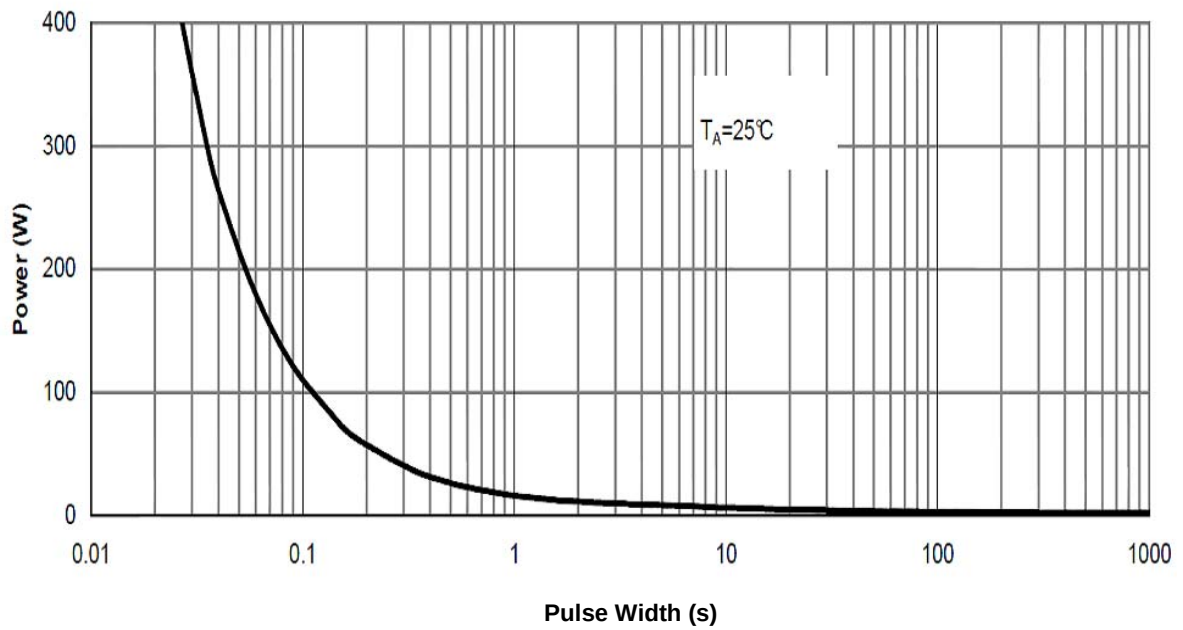


Figure 15: Single Pulse Power Rating Junction-Ambient

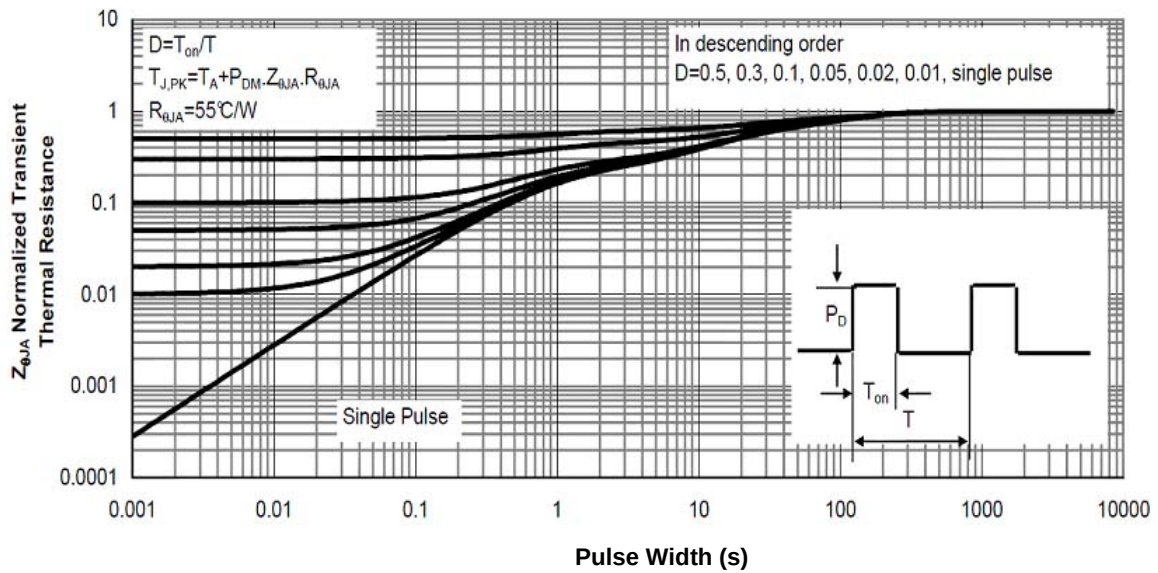
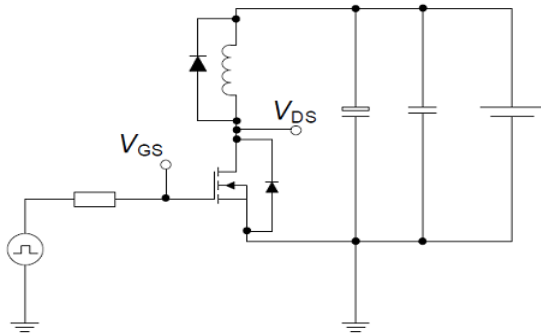


Figure 16: Normalized Maximum Transient Thermal Impedance

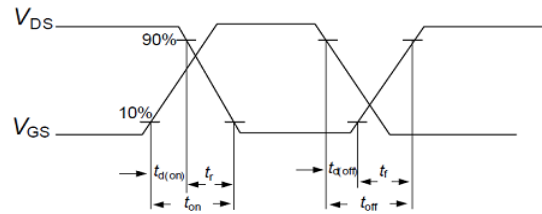
Test circuits

Switching times test circuit and waveform for inductive load

Switching times test circuit for inductive load

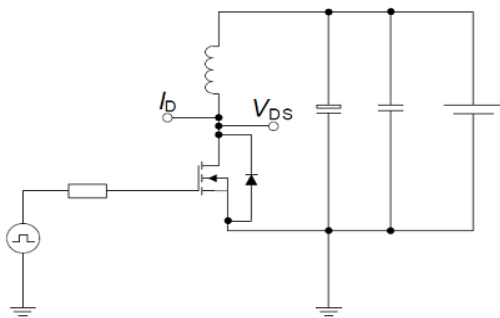


Switching time waveform

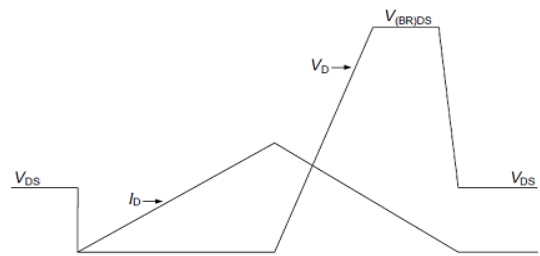


Unclamped inductive load test circuit and waveform

Unclamped inductive load test circuit

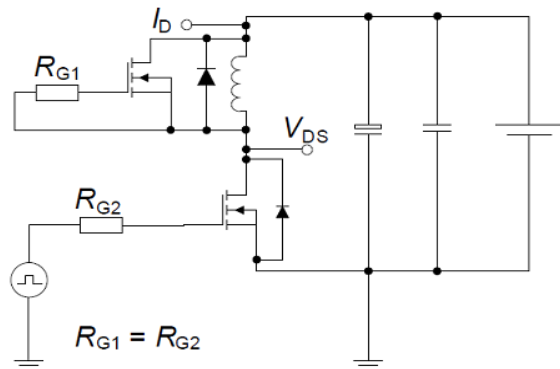


Unclamped inductive waveform

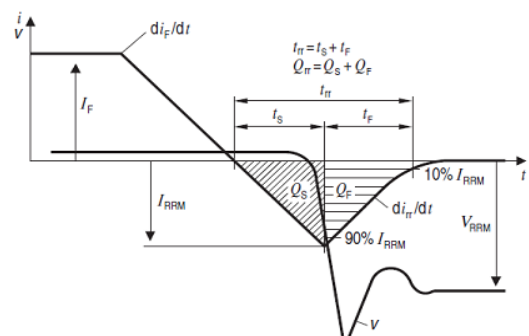


Test circuit and waveform for diode characteristics

Test circuit for diode characteristics



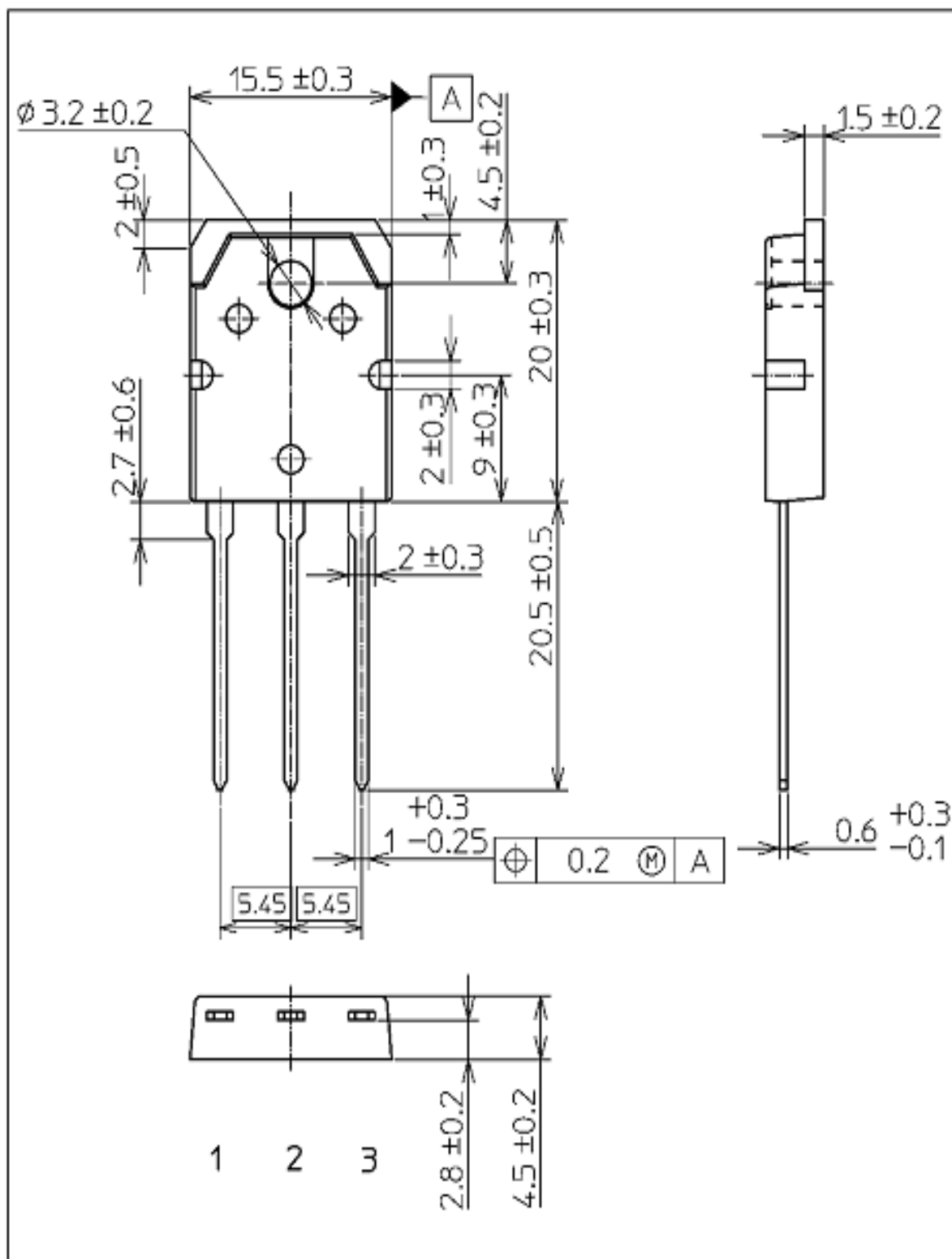
Diode recovery waveform



PKG TO-247

PKG TO-3P

Unit: mm



TSA20N60S, TSK20N60S600V N-Channel MOSFET

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